

THS9001

SLOS426A-NOVEMBER 2003-REVISED FEBRUARY 2004

50 MHz to 350 MHz CASCADEABLE AMPLIFIER

FEATURES

- High Dynamic Range
 - -OIP₃ = 36 dBm
 - -NF < 4.5 dB
- Single Supply Voltage
- High Speed
 - $V_S = 3 V to 5 V$
 - I_S = Adjustable
- Input / Output Impedance
 - **50** Ω

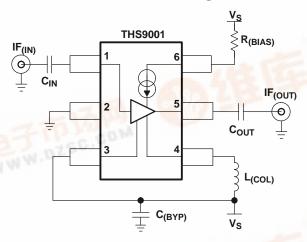
APPLICATIONS

- IF Amplifier
 - TDMA: GSM, IS-136, EDGE/UWE-136
 - CDMA: IS-95, UMTS, CDMA2000
 - Wireless Local Loop
 - Wireless LAN: IEEE802.11

DESCRIPTION

The THS9001 is a medium power, cascadeable, gain block optimized for high IF frequencies. The amplifier incorporates internal impedance matching to 50 Ω and achieves greater than 15-dB input and output return loss from 50 MHz to 350 MHz with $V_S = 5$ V, $R_{(BIAS)} = 237$ Ω , $L_{(COL)} = 470$ nH. Design requires only 2 dc-blocking capacitors, 1 power-supply bypass capacitor, 1 RF choke, and 1 bias resistor.

Functional Block Diagram



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS

PACKAGED DEVICES	PACKAGE TYPE	TRANSPORT MEDIA, QUANTITY
THS9001DBVT	SOT-23-6	Tape and Reel, 250
THS9001DBVR	501-23-6	Tape and Reel, 3000

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature (unless otherwise noted)(1)

		UNIT
Supply voltage, GND to	5.5 V	
Input voltage		GND to V _S
Continuous power dissip	pation	See Dissipation Ratings Table
Maximum junction temp	150°C	
Maximum junction temp	125°C	
Storage temperature, T _s	-65°C to 150°C	
Lead temperature 1,6 m	m (1/16 inch) from case for 10 seconds	300°C
	2000	
ESD Ratings	CDM	1500
	MM	100

⁽¹⁾ The absolute maximum ratings under any condition is limited by the constraints of the silicon process. Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

DISSIPATION RATING TABLE

PACKAGE	Θ_{JC}	Θ_{JA}	POWER RATING ⁽¹⁾			
PACKAGE	(₀C\M) ⊕ ^{∩C}	^Θ JA (°C/W)	T _A ≤ 25°C	T _A = 85°C		
DBV ⁽²⁾	70.1	216	463 mW	185 mW		

⁽¹⁾ Power rating is determined with a junction temperature of 125°C. Thermal management of the final PCB should strive to keep the junction temperature at or below 125°C for best performance.

RECOMMENDED OPERATING CONDITIONS

	MIN	NOM	MAX	UNIT
Supply voltage	2.7		5	V
Operating free-air temperature, T _A	-40		85	°C
Supply current		100		mA

⁽²⁾ The maximum junction temperature for continuous operation is limited by package constraints. Operation above this temperature may result in reduced reliability and/or lifetime of the device.

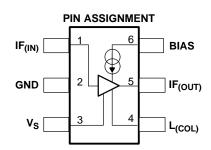
⁽²⁾ This data was taken using the JEDEC standard High-K test PCB.



ELECTRICAL CHARACTERISTICS

Typical Performance (V $_{\rm S}$ = 5 V, R $_{\rm (BIAS)}$ = 237 Ω , L $_{\rm (COL)}$ = 470 nH) (unless otherwise noted)

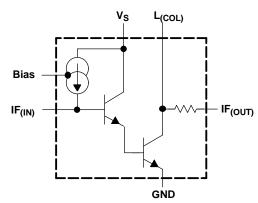
PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNITS
Gain	f = 50 MHz	15.8	dB
Gain	f = 350 MHz	15.0	UB UB
OID	f = 50 MHz	35	dDm
OIP ₃	f = 350 MHz	37	dBm
1 dD compression	f = 50 MHz	20.6	dDm
1-dB compression	f = 350 MHz	20.6	dBm
Lamest materials lames	f = 50 MHz	15.4	dB
Input return loss	f = 350 MHz	16.6	UB UB
Output ratura laga	f = 50 MHz	17	٩D
Output return loss	f = 350 MHz	15	dB
Reverse isolation	f = 50 MHz	20.7	٩D
Reverse isolation	f = 350 MHz	20.7	dB
N	f = 50 MHz	3.7	40
Noise figure	f = 350 MHz	4	dB



Terminal Functions

Pin Numbers	Name	Description
1	IF _(IN)	Signal input
2	GND	Negative power supply input
3	V _S	Positive power supply input
4	L _(COL)	Output transistor load inductor
5	IF _(OUT)	Signal output
6	BIAS	Bias current input

SIMPLIFIED SCHEMATIC



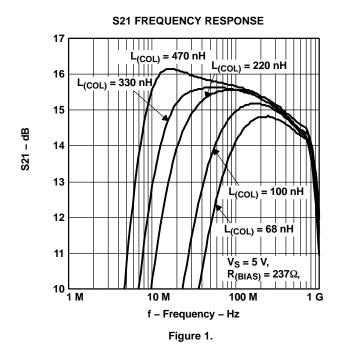


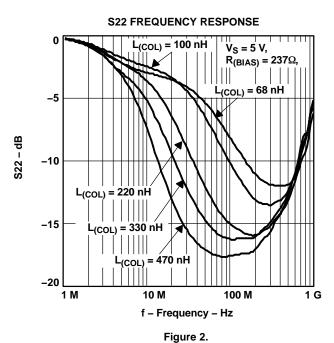
TYPICAL CHARACTERISTICS

TABLE OF GRAPHS

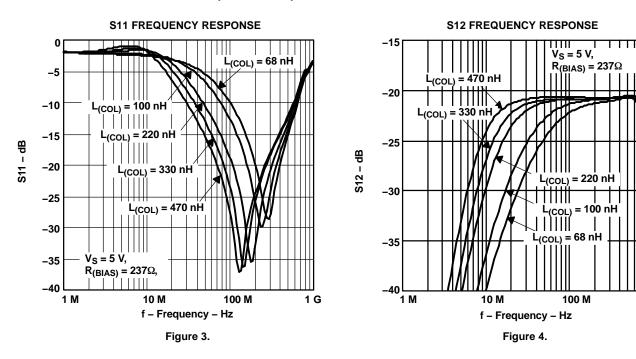
		FIGURE
	S21 Frequency response	1
	S22 Frequency response	2
	S11 Frequency response	3
	S12 Frequency response	4
	S21 vs R _(Bias)	5
	Output power vs Input power	6
	OIP ₂ vs Frequency	7
	Noise figure vs Frequency	8
	OIP ₃ vs Frequency	9
I _S	Supply current vs R _(Bias)	10
	S21 Frequency response	11
	S22 Frequency response	12
	S11 Frequency response	13
	S12 Frequency response	14
	Noise figure vs Frequency	15
	OIP ₂ vs Frequency	16
	Output power vs Input power	17
	OIP ₃ vs Frequency	18

S-Parameters of THS9001 as mounted on the EVM with V_S = 5 V, $R_{(BIAS)}$ = 237 Ω , and $L_{(COL)}$ = 68 nH to 470 nH at room temp.

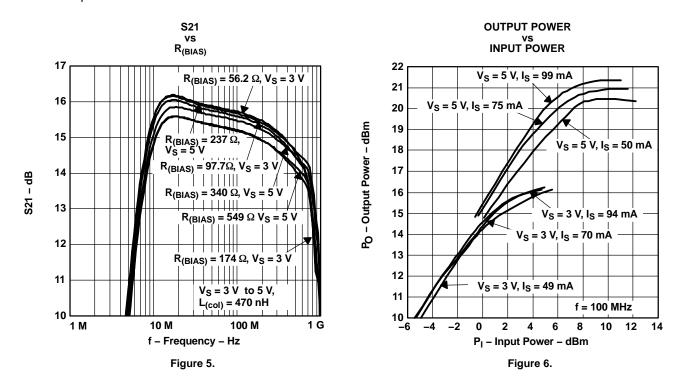




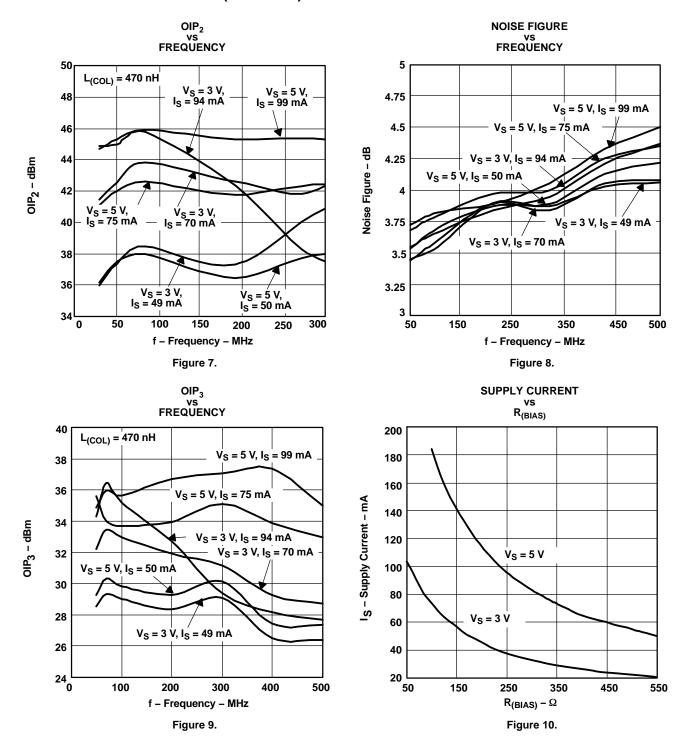




S-Parameters of THS9001 as mounted on the EVM with $V_S = 3$ V and 5 V, $R_{(BIAS)} = various$, and $L_{(COL)} = 470$ nH at room temp.

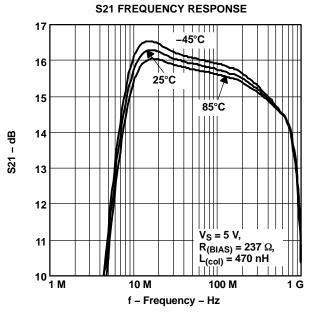




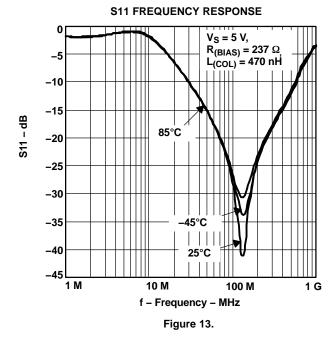




THS9001 as mounted on the EVM with V_S = 5 V, $R_{(BIAS)}$ = 237 Ω , and $L_{(COL)}$ = 470 nH at 40°C, 25°C, and 85°C.







S22 FREQUENCY RESPONSE

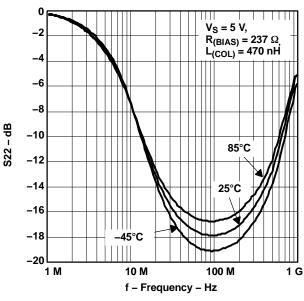
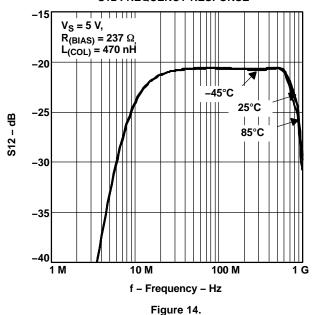


Figure 12.

S12 FREQUENCY RESPONSE



rigure 14.



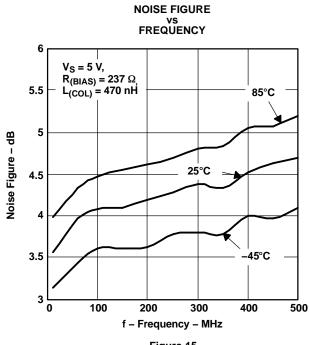
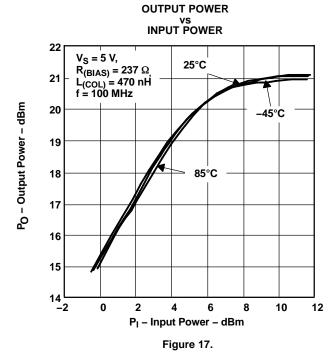


Figure 15.



OIP₂ vs FREQUENCY 48 $V_S = 5 V$ $R_{(BIAS)} = 237 \Omega$ $L_{(COL)} = 470 \text{ nH}$ -45°C 47 46 45 25°C 85°C 44 43 42 41 40 100 150 200 250 300 50 f - Frequency - MHz

 OIP_2 – dBm

Figure 16.

OIP₃

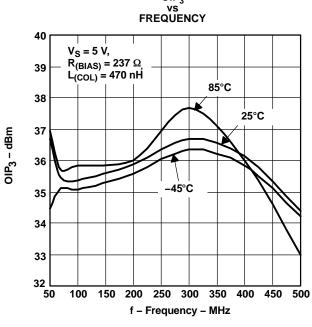


Figure 18.



TYPICAL CHARACTERISTICS

S-Parameters Tables of THS9001 with EVM De-Embedded

S21		521	S	11	S	22	S	12
Frequency (MHz)	Gain (dB)	Phase (deg)						
1.0	-3.5	-165.0	-2.3	-1.1	-2.6	174.8	-64.4	-121.7
5.0	11.7	-127.1	-1.5	-14.9	-2.8	140.4	-32.4	123.0
10.2	15.8	-150.1	-2.2	-42.3	-5.3	99.8	-23.6	79.5
19.7	16.3	-170.8	-6.6	-69.3	-10.7	64.5	-21.1	40.7
50.1	15.9	175.7	-16.2	-90.3	-16.2	33.9	-20.6	14.5
69.7	15.8	171.5	-21.1	-95.4	-16.9	26.4	-20.6	9.4
102.4	15.7	165.7	-32.3	-86.5	-17.1	19.9	-20.6	5.3
150.5	15.6	158.2	-28.0	45.9	-16.8	14.7	-20.7	2.1
198.1	15.5	151.1	-21.9	46.8	-16.2	10.8	-20.7	0.1
246.9	15.3	144.1	-18.9	37.2	-15.3	6.0	-20.7	-1.4
307.6	15.2	135.3	-16.0	27.8	-14.2	-1.8	-20.6	-3.9
362.8	15.0	127.8	-14.2	17.4	-13.3	-9.2	-20.6	-5.9
405.0	14.9	121.9	-12.8	10.9	-12.6	-16.0	-20.6	-8.2
452.2	14.7	115.4	-11.6	3.0	-11.8	-23.9	-20.6	-10.8
504.7	14.5	108.4	-10.3	-6.0	-10.9	-33.0	-20.7	-14.2
563.4	14.4	100.3	-8.9	-17.4	-9.8	-45.2	-20.9	-19.3
595.3	14.2	96.0	-8.2	-23.3	-9.2	-52.2	-21.0	-22.6
664.5	14.1	87.0	-6.7	-36.9	-8.0	-68.3	-21.7	-30.5
702.1	14.0	80.9	-5.9	-44.6	-7.3	-79.1	-22.5	-38.6
741.8	13.9	76.5	-5.1	-54.0	-6.8	-91.4	-24.0	-44.9
828.1	13.5	62.2	-4.3	-76.1	-6.3	-113.2	-26.5	-35.0
874.9	13.0	54.0	-4.1	-84.6	-5.9	-126.0	-27.0	-49.0
924.4	12.8	44.9	-3.6	-93.1	-5.1	-136.8	-28.0	-62.9
976.7	11.6	35.9	-3.5	-104.4	-5.3	-157.8	-34.0	-104.4
1031.9	11.1	33.0	-3.4	-115.7	-5.8	-172.3	-37.1	107.9
1090.3	10.4	29.2	-3.3	-122.0	-5.7	-173.4	-37.8	162.5
1151.9	10.3	22.2	-3.0	-131.3	-4.8	179.4	-31.1	169.5
1217.1	9.7	4.7	-2.9	-142.3	-3.9	161.9	-26.3	137.1
1285.9	8.6	0.7	-2.9	-151.7	-3.6	147.6	-22.7	121.9
1358.6	7.3	-8.3	-2.9	-161.2	-3.4	134.6	-20.6	116.5
1435.5	5.8	-14.5	-3.0	-170.1	-3.2	122.6	-18.8	105.2
1516.6	4.6	-22.7	-3.1	-178.6	-3.2	112.1	-17.2	96.0
1602.4	3.2	-28.4	-3.1	173.2	-3.1	101.7	-15.7	87.0
1693.0	1.5	-38.0	-3.1	165.1	-3.0	92.4	-14.3	79.2
1788.8	-0.5	-47.9	-3.1	157.6	-2.9	83.6	-13.1	68.8
1889.9	-2.5	-51.0	-3.2	148.8	-2.7	74.4	-12.4	56.9
1996.8	-4.1	-49.0	-3.4	139.5	-2.3	65.0	-12.2	48.2

APPLICATION INFORMATION

The THS9001 is a medium power, cascadeable, amplifier optimized for high intermediate frequencies in radios. The amplifier is unconditionally stable and design requires only 2 dc-blocking capacitors, 1 power-supply bypass capacitor, 1 RF choke, and 1 bias resistor. Refer to Figure 24 for circuit diagram.

The THS9001 operates with a power supply voltage ranging from 2.5 V to 5.5 V.

The value of $R_{(BIAS)}$ sets the bias current to the amplifier. Refer to Figure 10. This allows the designer to trade-off linearity versus power consumption. $R_{(BIAS)}$ can be removed without damage to the device.

Component selection of $C_{(BYP)}$, C_{IN} , and C_{OUT} is not critical. The values shown in Figure 24 were used for all the data shown in this data sheet.

The amplifier incorporates internal impedance matching to 50 Ω that can be adjusted for various frequencies of operation by proper selection of L_(COL).

Figure 19 shows the s-parameters of the part mounted on the standard EVM with $V_S = 5$ V, $R_{(BIAS)} = 237\Omega$, and $L_{(COL)} = 470$ nH. With this configuration, the part is very broadband, and achieves greater than 15-dB input and output return loss from 50 MHz to 325 MHz.

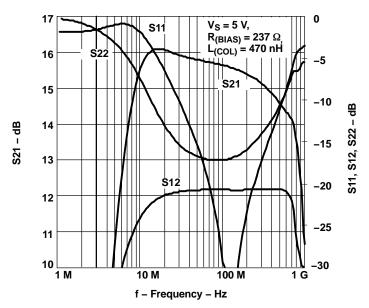


Figure 19. S-Parameters of THS9001 Mounted on the Standard EVM With V $_{\rm S}$ = 5 V, R $_{\rm (BIAS)}$ = 237 $\Omega,$ and L $_{\rm (COL)}$ = 470 nH



APPLICATION INFORMATION (continued)

Figure 20 Shows an example of a single conversion receiver architecture and where the THS9001 would typically be used.

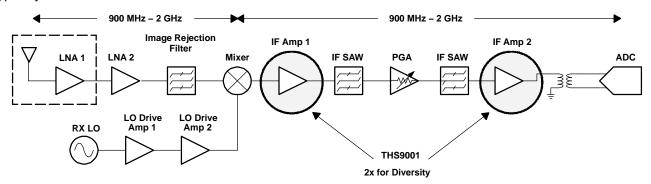


Figure 20. Example Single Conversion Receiver Architecture

Figure 21 shows an example of a dual conversion receiver architecture and where the THS9001 would typically be used.

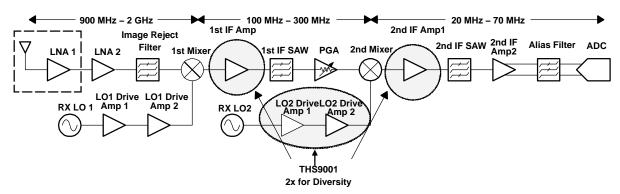


Figure 21. Example Dual Conversion Receiver Architecture

Figure 22 shows an example of a dual conversion transmitter architecture and where the THS9001 would typically be used.

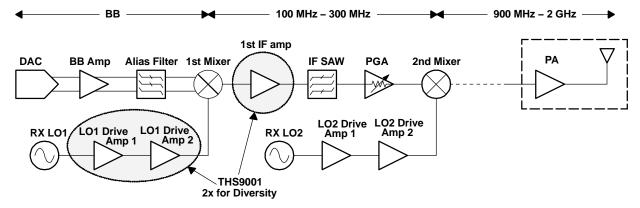


Figure 22. Example Dual Conversion Transmitter Architecture

APPLICATION INFORMATION (continued)

Figure 23 shows the THS9001 and Sawtek #854916 SAW filter frequency response along with the frequency response of the SAW filter alone. The SAW filter has a center frequency of 140 MHz with 10-MHz bandwidth and 8-dB insertion loss. It can be seen that the frequency response with the THS9001 is the same as with the SAW except for a 15-dB gain. The THS9001 is mounted on the standard EVM with $V_S = 5$ V, $R_{(BIAS)} = 237$ Ω , and $L_{(COL)} = 470$ nH. Note the amplifier does not add artifacts to the signal.

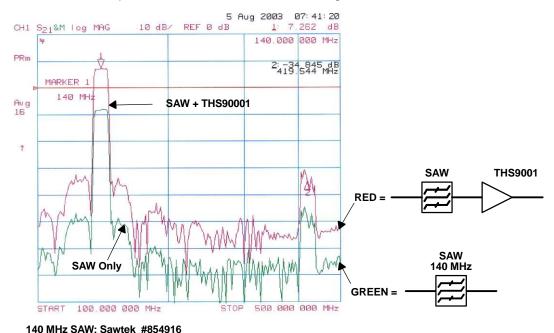


Figure 23. Frequency Response of the THS9001 and SAW Filter, and SAW Filter Only

THS9001 $R_{(BIAS)}$ $R_{(BIAS)}$

Figure 24. THS9001 Recommended Circuit (Used for all Tests)



APPLICATION INFORMATION (continued)

Evaluation Module

Table 1 is the bill of materials, and Figure 25 and Figure 26 show the EVM layout.

Bill Of Materials

ITEM	DESCRIPTION	REF DES	QTY	PART NUMBER (1)
1	Cap, 0.1 μF, ceramic, X7R, 50 V	C1	1	(AVX) 08055C104KAT2A
2	Cap, 1000 pF, ceramic, NPO, 100 V	C2, C3	2	(AVX) 08051A102JAT2A
3	Inductor, 470 nH, 5%	L1	1	(Coilcraft) 0805CS-471XJBC
4	Resistor, 237 Ω, 1/8 W, 1%	R1	1	(Phycomp) 9C08052A2370FKHFT
5	Open	TR1	1	
6	Jack, banana receptance, 0.25" dia.	J3, J4	2	(SPC) 813
7	Connector, edge, SMA PCB jack	J1, J2	2	(Johnson) 142-0701-801
8	Standoff, 4-40 Hex, 0.625" Length		4	(KEYSTONE) 1808
9	Screw, Phillips, 4-40, .250"		4	SHR-0440-016-SN
10	IC, THS9001	U1	1	(TI) THS9001DBV
11	Board, printed-circuit		1	(TI) EDGE # 6453522 Rev.A

(1) The manufacturer's part numbers are used for test purposes only.

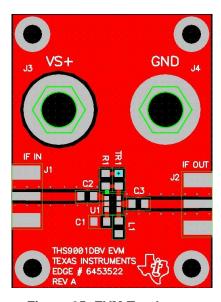


Figure 25. EVM Top Layout

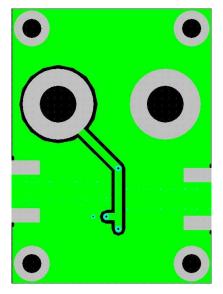


Figure 26. EVM Bottom Layout



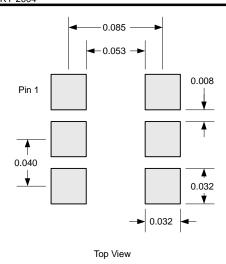


Figure 27. THS9001 Recommended Footprint (dimensions in inches)



PACKAGE OPTION ADDENDUM

14-Mar-2006

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
THS9001DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS9001DBVRG4	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS9001DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS9001DBVTG4	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

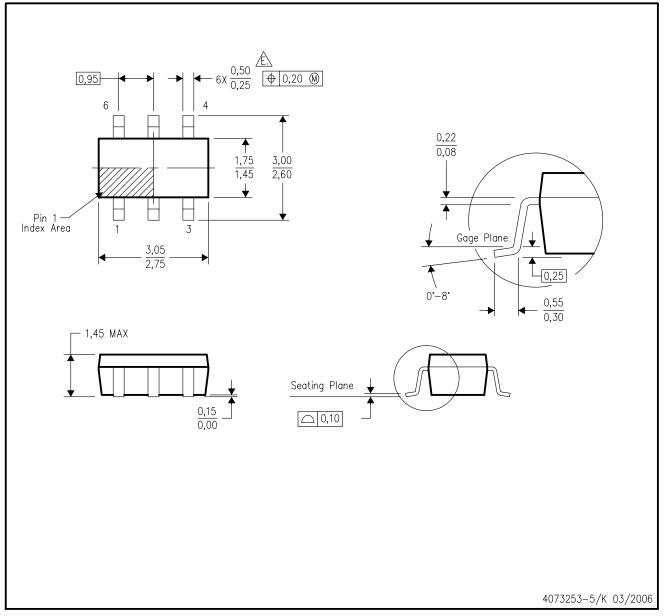
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side. D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



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Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
		Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
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